

## Background

- Power Overlay (POL) Technology
  - Utilizes flexible polyimide substrate & direct metal interconnects to eliminate wire-bonds and solder interfaces
  - Currently used in high density power devices & modules, RF modules, application specific ICS (ASICs), & sensing devices [1,2]
- POL for LED packages
  - Direct bonding of LED dies to polyimide substrate with use of adhesive
  - Thermal vias used to provide efficient thermal path from die to contact pad

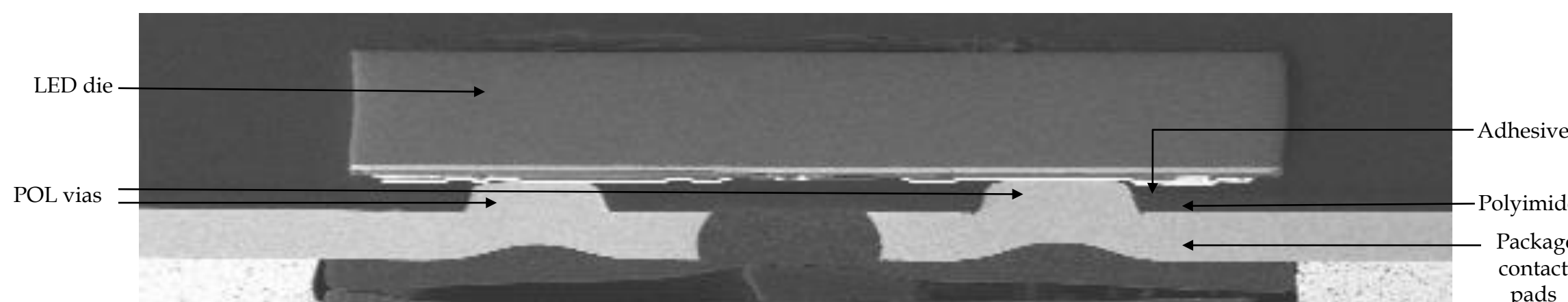


Figure 1: SEM image of the cross-section of the LED prototype manufactured using POL – kw packaging technology

## Objectives

- Evaluate and optimize the use of POL-kw packaging technology for high power LED applications
  - Study effect of geometry parameters & substrate material on LED prototype
  - Estimate PCB level thermal performance of LED prototype using FEA
  - Experimentally validate simulation model using infrared tomography

## Methodology

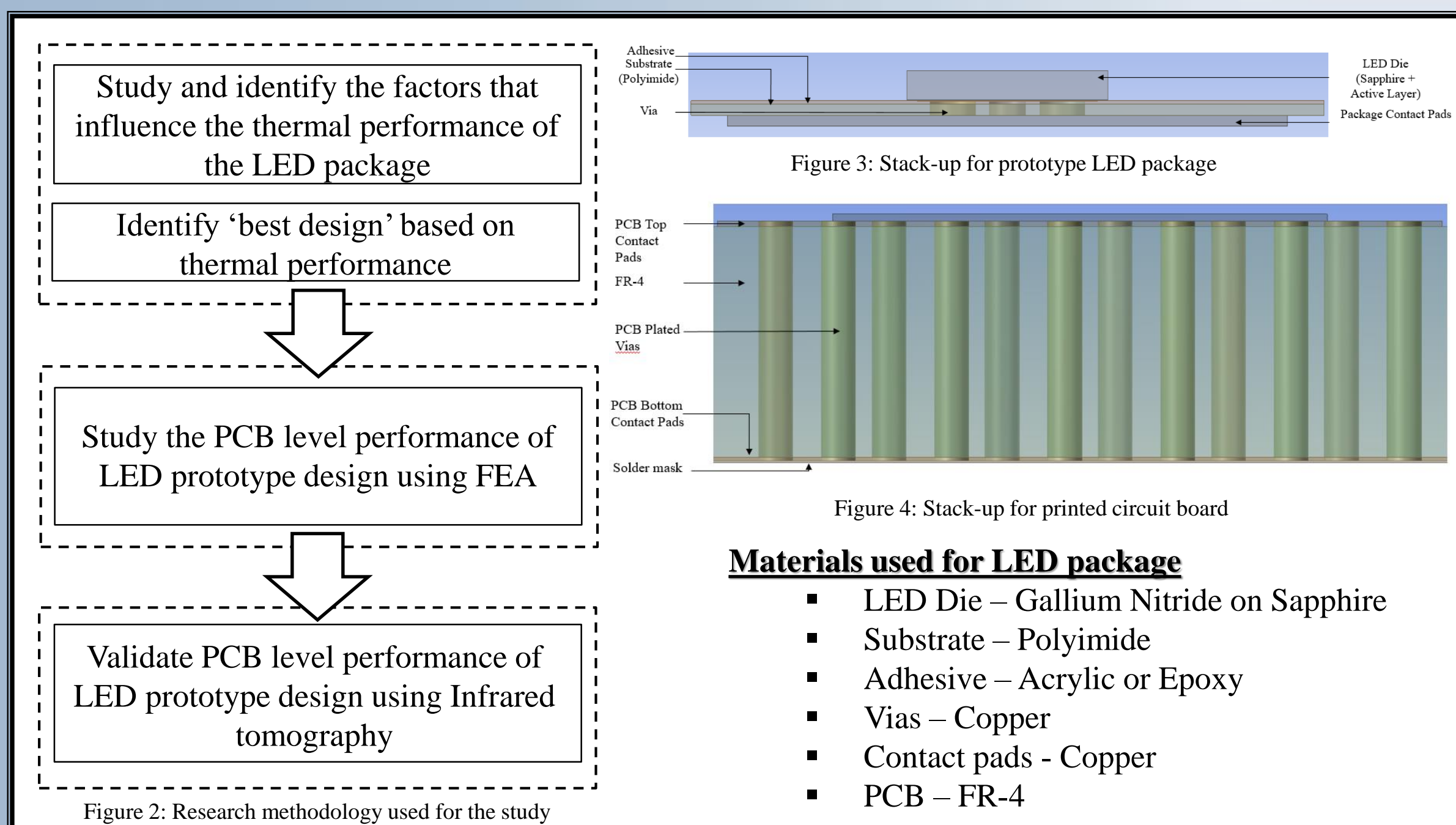


Figure 2: Research methodology used for the study

## Results

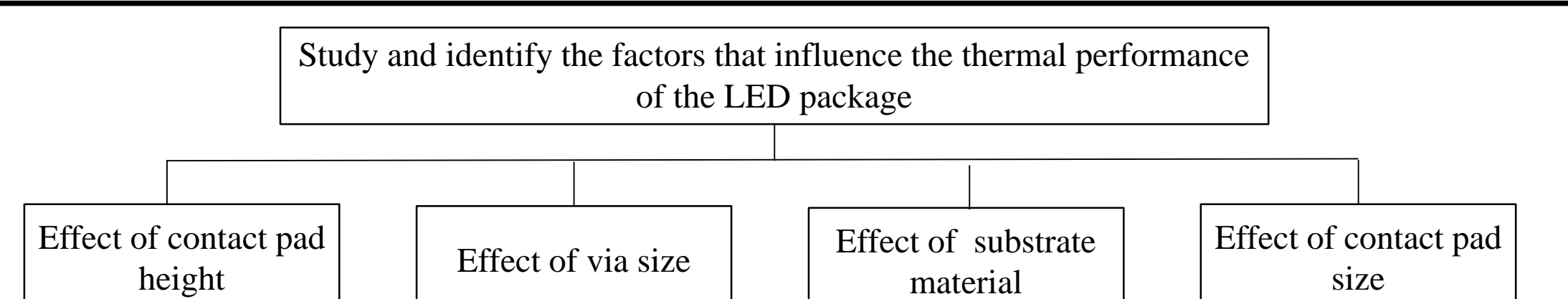


Figure 5: Factors studied for the LED prototype design

Factor	Factor levels	
	+	-
Contact pad height	100 $\mu\text{m}$	50 $\mu\text{m}$
Via size	0.200-0.250 $\mu\text{m}$	0.100-0.150 $\mu\text{m}$
Substrate material	Polyimide (0.12 W/ $^{\circ}\text{C}$ )	Aluminum Nitride (180 W/ $^{\circ}\text{C}$ )
Contact pad size	1.46 x 3.07 mm	1 x 1.5 mm

Figure 6: Table for factor name and factor levels of the LED prototype design studied

### Analysis of Variance

Source	DF	Adj SS	Adj MS	F-Value	P-Value
Model	10	739.304	73.930	40642.03	0.000
Linear	4	729.722	182.430	100288.20	0.000
Contact pad height	1	1.289	1.289	708.49	0.000
Via size	1	701.707	701.707	385751.92	0.000
Substrate material	1	26.726	26.726	14692.36	0.000
Contact pad size	1	0.000	0.000	0.01	0.916
2-Way Interactions	6	9.582	1.597	877.93	0.000
Contact pad height*Via size	1	0.034	0.034	18.76	0.007
Contact pad height*Substrate material	1	0.060	0.060	32.93	0.002
Contact pad height*Contact pad size	1	0.000	0.000	0.00	0.996
Via size*Substrate material	1	9.488	9.488	5215.84	0.000
Via size*Contact pad size	1	0.000	0.000	0.02	0.907
Substrate material*Contact pad size	1	0.000	0.000	0.02	0.907
Error	5	0.009	0.002		
Total	15	739.313			

Figure 7: ANOVA table for analyzing the significant factors that influence the average surface temperature of the LED prototype

- The contact pad height, via size, & substrate material are the most significant factors that affect the thermal performance of the LED prototype

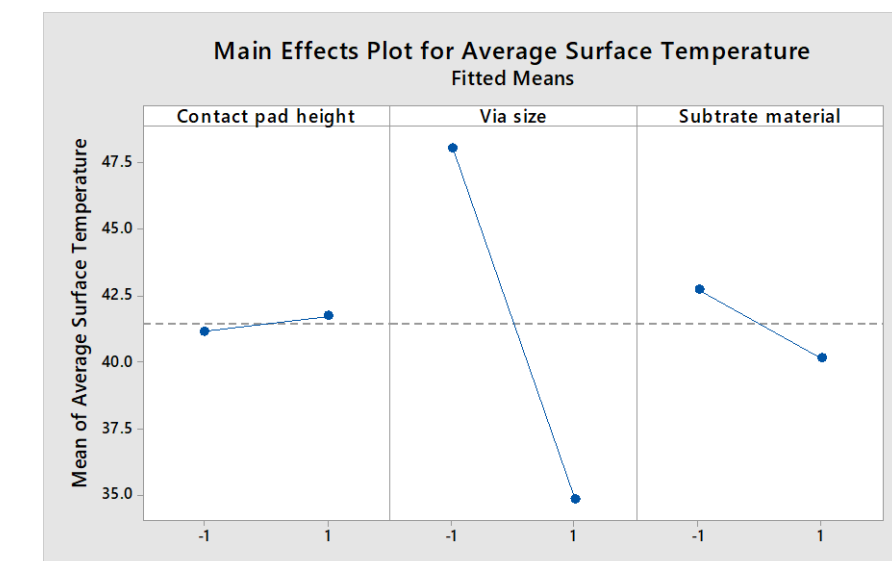


Figure 8: Main effect plot significant factors that influence the average surface temperature of the LED prototype

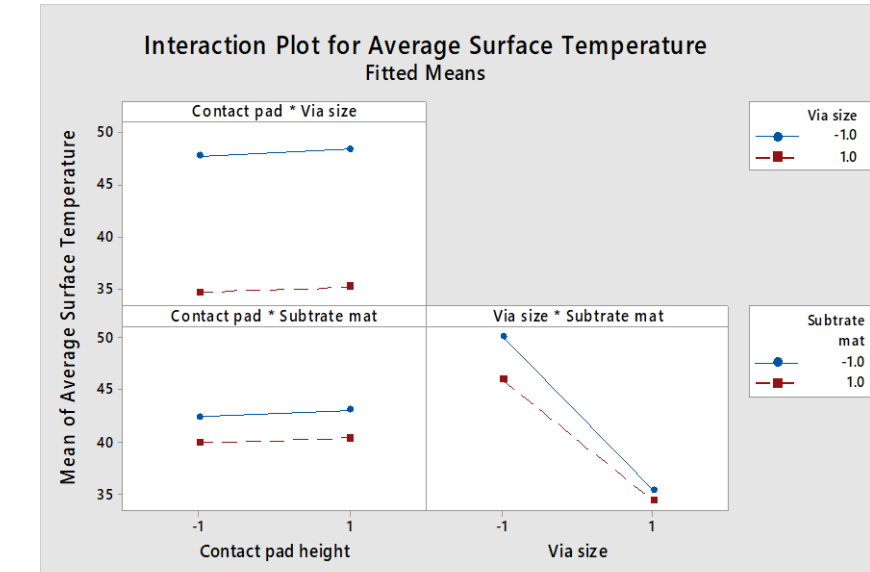


Figure 9: Interaction effect plot significant factors that influence the average surface temperature of the LED prototype

## Results (Experimentally Measured)

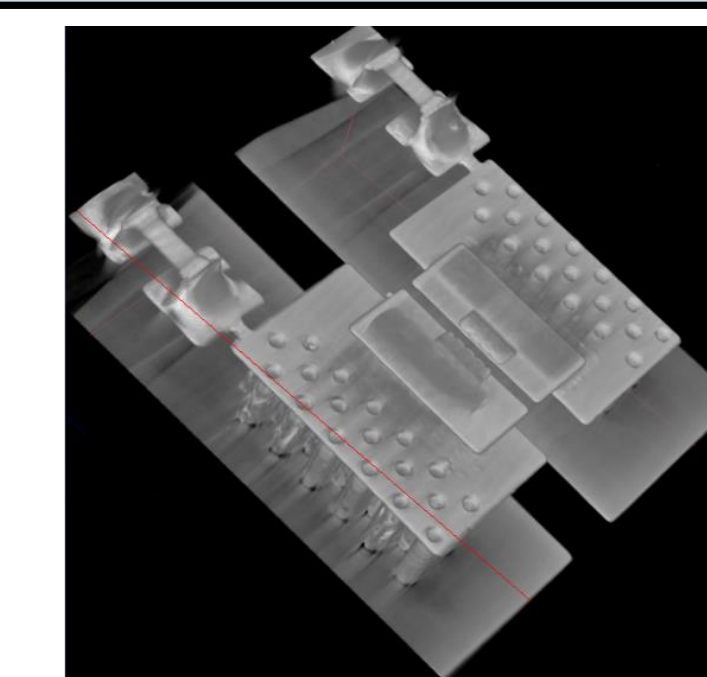


Figure 14: X-Ray image of the POL LED prototype assembled on a PCB

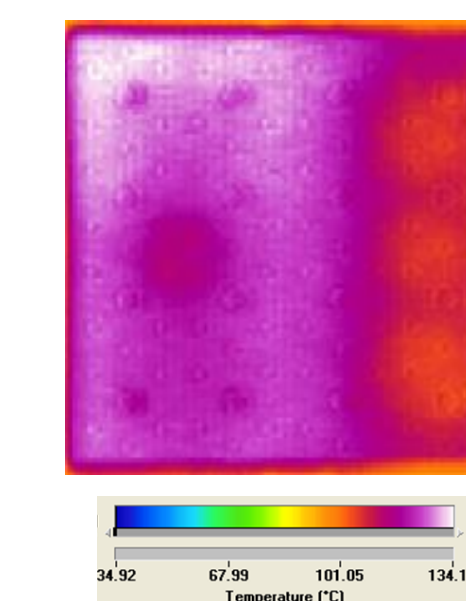


Figure 15: Temperature map of the surface of the LED die at input current of 1A

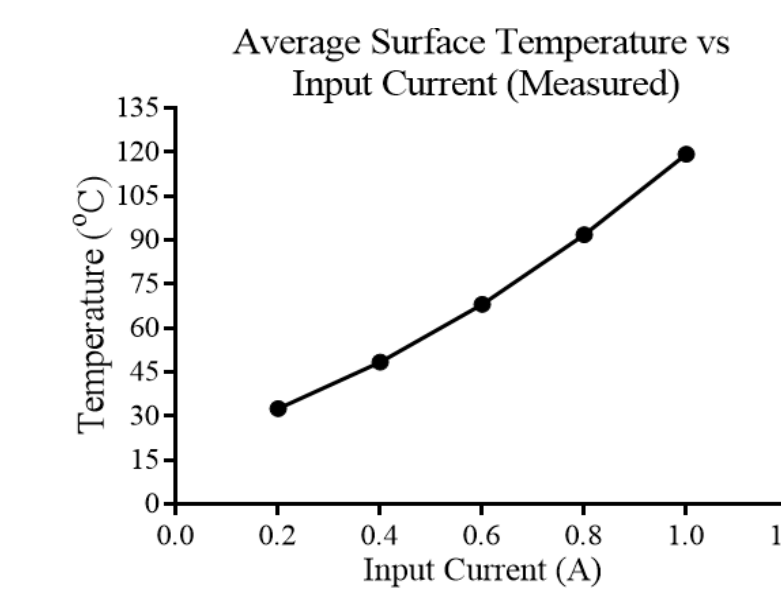


Figure 16: Surface temperature LED die at different input currents

## Conclusions

- Efficient thermal architecture is key to effective thermal management
- Low thermal conductivity of polyimide substrate is the most significant bottleneck in effective thermal management in flexible LED packages
- Increase in size of vias & reduction in contact pad height reduced average temperature of LED prototype
- Increase in size of contact pad did not provide any additional heat spreading benefits
- Temperatures estimated by FEA are validated by temperature measurements using infrared tomography & are in agreement with the FEA model based on average chip temperatures
- Experimental results show slightly higher temperature on cathode side of LED die

## Results (FEA Analysis)

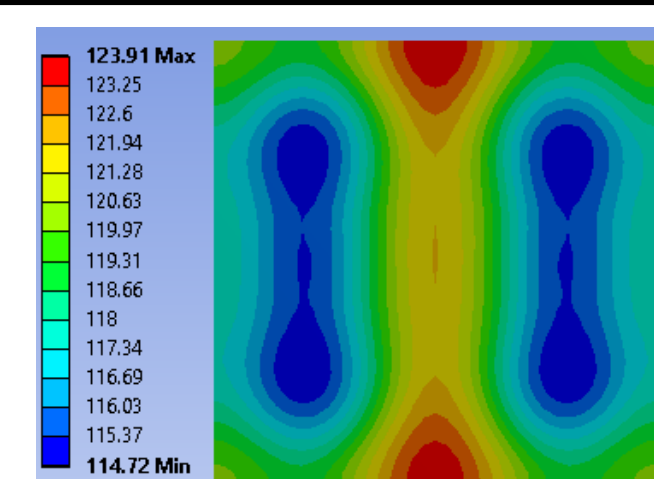


Figure 10: Temperature map of the top surface of the sapphire layer on LED die at input current of 1A

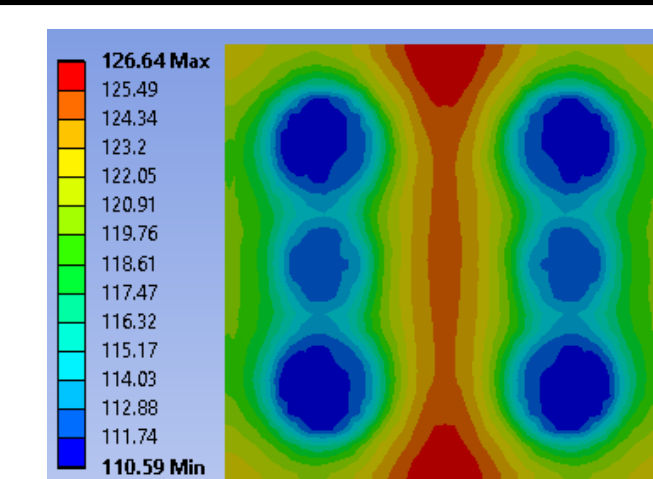


Figure 11: Temperature map of the top surface of the active layer (GaN) in LED die at input current of 1A

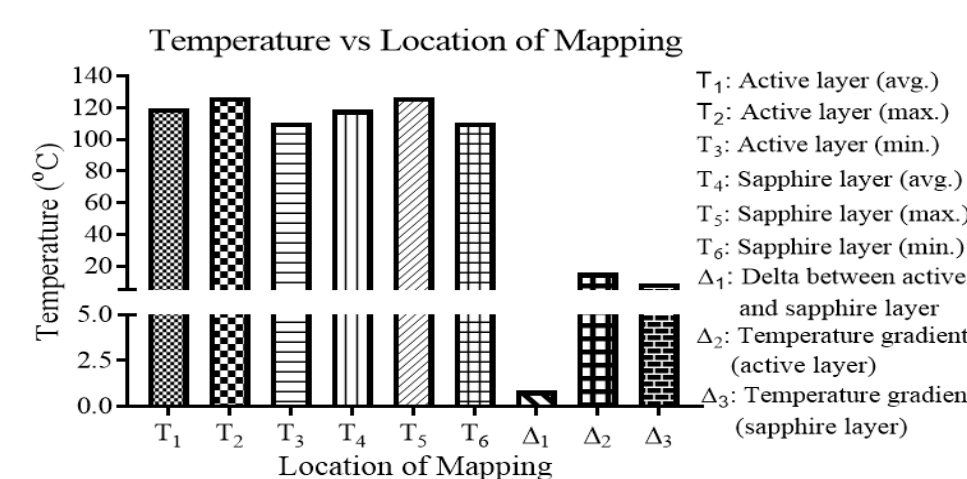


Figure 12: Temperature of active layer (GaN) & sapphire layer at input currents of 1A

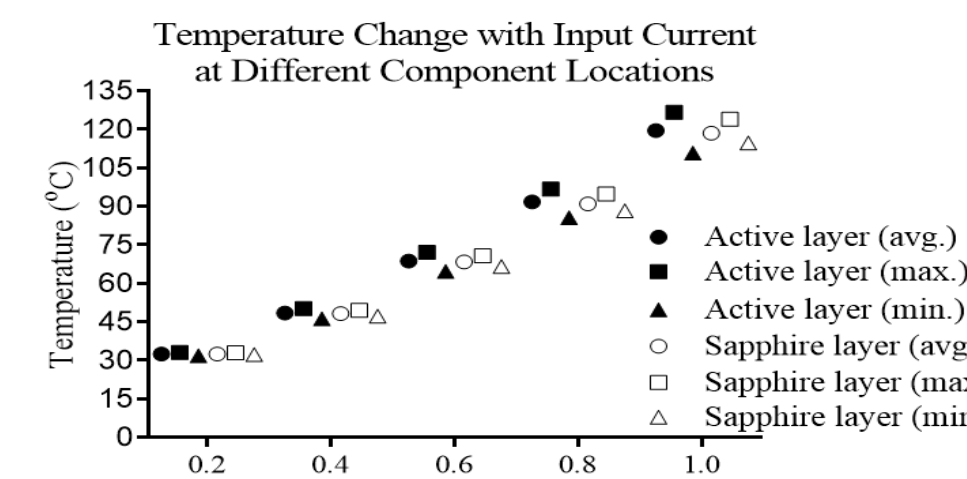


Figure 13: Temperature of active layer (GaN) & sapphire layer at different input currents

## Acknowledgements

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## References

[1] A. Gowda, S. Chauhan, P. McConnelee, K. Chris and Y. Lee, "Power Overlay Packaging Platform for High Performance Electronics," *Chip Scale Review*, pp. 22-27, 19 September 2012

[2] B. Ozmat, C. S. Korman and R. Fillion, "An advanced approach to power module packaging," in *International Workshop on Integrated Power Packaging*, Waltham, 2000